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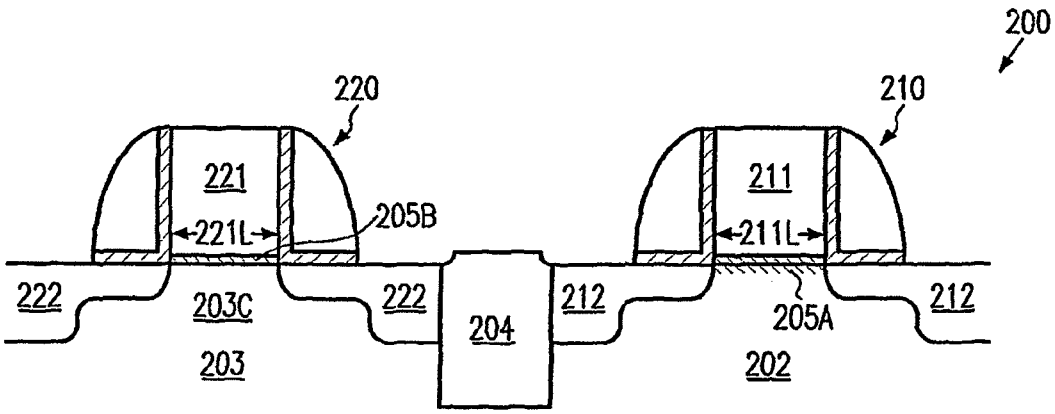
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(54) Title: A SEMICONDUCTOR DEVICE HAVING A GATE DIELECTRIC OF DIFFERENT BLOCKING CHARACTERISTICS




(57) Abstract: By locally adapting the blocking capability of gate insulation layers 205A, 205B for N-channel transistors and P-channel transistors, the reliability and threshold stability of the P-channel transistor may be enhanced, while nevertheless electron mobility of the N-channel transistor may be kept at a high level. This may be accomplished by incorporating a different amount of a dielectric dopant into respective gate insulation layer portions 205A, 205B.

WO 2006/118787 A1